I hereby certify that this correspondence is being deposited with the U.S. Postal Service with sufficient postage as First Class Mail, in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on the date shown below.

Dated: April 25, 2005

JE . 7

Signature:

Docket No.: 29936/39485

(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Kwan Yong Lim et al.

Application No.: 10/615,478

Confirmation No.: 9262

Art Unit: 2829 Filed: July 8, 2003

Examiner: Asok K. Sarkar METHOD OF FORMING GATE IN For:

SEMICONDUCTOR DEVICE

INFORMATION DISCLOSURE STATEMENT (IDS)

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 CFR 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the 'References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is filed after the mailing date of the first Office Action on the merits but before the mailing date of a Final Office Action or Notice of Allowance (37 CFR 1.97(c)).

I hereby certify that each item of information contained in this Information Disclosure Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement.

Application No.: 10/615,478 Docket No.: 29936/39485

A summary of the non-English language reference (1999-46953) is as follows. Korean Patent Publication No. 1999-46953 is directed to a method of manufacturing a transistor of a semiconductor device and, more particularly, to a method of manufacturing a MOS transistor of a lightly doped drain structure, in which a thickness of an oxide film between a sidewall spacer and a silicon substrate can be controlled such that a hot carrier which flows into the thin oxide film located between a gate electrode and a silicon substrate is reduced and the dependability of the semiconductor device is enhanced.

A copy of each reference on the PTO/SB/08 is attached.

In accordance with 37 CFR 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 CFR 1.56(a) exists. In accordance with 37 CFR 1.97(h), the filing of this Information Disclosure statement shall not be construed to be an admission that any patent, publication or other information referred to therein is "prior art" for this invention unless specifically designated as such.

It is submitted that the Information Disclosure Statement is in compliance with 37 CFR 1.98 and the Examiner is respectfully requested to consider the listed references.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 13-2855, under Order No. 29936/39485. A duplicate copy of this paper is enclosed.

By

Dated: April 25, 2005

Respectfully submitted,

Michael R. Hull

Registration No.: 35,902

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PTO/SB/08a/b (08-03)

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Substitute for form 1449A/B/PTO				Complete if Known		
				Application Number	10/615,478-Conf. #9262	
11	NFORMATIC	N DISC	CLOSURE	Filing Date	July 8, 2003	
STATEMENT BY APPLICANT			PLICANT	First Named Inventor	Kwan Y. Lim	
	(Use as many sheets as necessary)			Art Unit	2829	
				Examiner Name	Asok K. Sarkar	
Sheet	1	of	1	Attorney Docket Number	29936/39485	

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.1	Document Number Number-Kind Code ² (<i>if known</i>)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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FOREIGN PATENT DOCUMENTS						
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		KR-1999-46953	07-05-1999			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS				
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Application No. (if known): 10/615,478

Attorney Docket No.: 29936/39485

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April 25, 2005

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